



BD175 BD176
BD177 BD178
BD179 BD180

EPITAXIAL-BASE NPN/PNP

MEDIUM POWER LINEAR AND SWITCHING APPLICATIONS

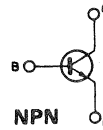
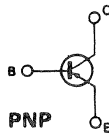
The BD175, BD177 and BD179 are silicon epitaxial-base NPN power transistors in Jedec TO-126 plastic package intended for use in medium power linear and switching applications. The complementary PNP types are the BD176, BD178 and BD180.

ABSOLUTE MAXIMUM RATINGS

| | | NPN PNP* | BD175 BD176 | BD177 BD178 | BD179 BD180 |
|-----------|---|-------------|----------------|----------------|----------------|
| V_{CBO} | Collector-base voltage ($I_E = 0$) | | 45V | 60V | 80V |
| V_{CEO} | Collector-emitter voltage ($I_B = 0$) | | 45V | 60V | 80V |
| V_{EBO} | Emitter-base voltage ($I_C = 0$) | | | 5V | |
| I_C | Collector current | | | 3A | |
| I_{CM} | Collector peak current | | | 7A | |
| P_{tot} | Total power dissipation at $T_{case} \leq 25^\circ C$ | | | 30V | |
| T_{stg} | Storage temperature | | | -65 to 150°C | |
| T_j | Junction temperature | | | 150°C | |

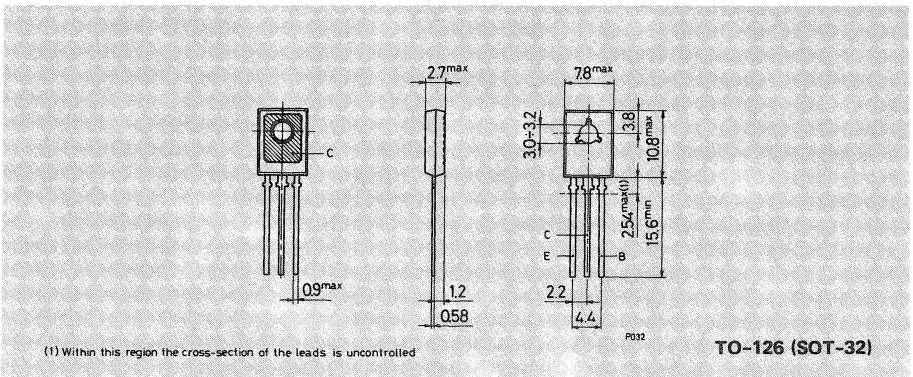
* For PNP types voltage and current are negative

INTERNAL SCHEMATIC DIAGRAMS



MECHANICAL DATA

Dimensions in mm



TO-126 (SOT-32)



BD175 BD176
BD177 BD178
BD179 BD180

THERMAL DATA

| | | | |
|-------------------------|----------------------------------|-----|-----------|
| $R_{th \text{ J-case}}$ | Thermal resistance junction-case | max | 4.16 °C/W |
|-------------------------|----------------------------------|-----|-----------|

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}\text{C}$ unless otherwise specified)

| Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|---|---|-----------------|-------------------|-------------------|---|
| I_{CBO} Collector cutoff current ($I_E = 0$) | for BD175/76 $V_{CB} = 45\text{V}$ for BD177/78 $V_{CB} = 60\text{V}$ for BD179/80 $V_{CB} = 80\text{V}$ | | | 100 100 100 | μA μA μA |
| I_{EBO} Emitter cutoff current ($I_C = 0$) | $V_{EB} = 5\text{V}$ | | | 1 | mA |
| $V_{CEO(sus)}^*$ Collector-emitter sustaining voltage | $I_C = 100\text{mA}$ for BD175/76 for BD177/78 for BD179/80 | 45 60 80 | | | V V V |
| $V_{CE(sat)}^*$ Collector-emitter saturation voltage | $I_C = 1\text{A}$ $I_B = 0.1\text{A}$ | | | 0.8 | V |
| V_{BE}^* Base-emitter volt. | $I_C = 1\text{A}$ $V_{CE} = 2\text{V}$ | | | 1.3 | V |
| h_{FE}^* DC current gain | $I_C = 150\text{mA}$ $V_{CE} = 2\text{V}$ $I_C = 1\text{A}$ $V_{CE} = 2\text{V}$ | 40 15 | | | — — |
| h_{FE} groups** | $I_C = 150\text{mA}$ $V_{CE} = 2\text{V}$ | 40 63 100 | 100 160 250 | | — — — |
| f_T Transition freq. | $I_C = 250\text{mA}$ $V_{CE} = 10\text{V}$ | 3 | | | MHz |

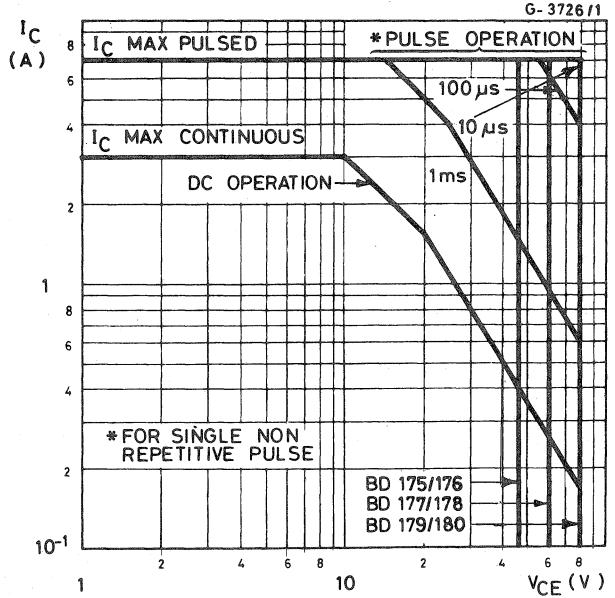
* Pulsed: pulse duration = $300\mu\text{s}$, duty cycle $\leq 1.5\%$

** Only on request

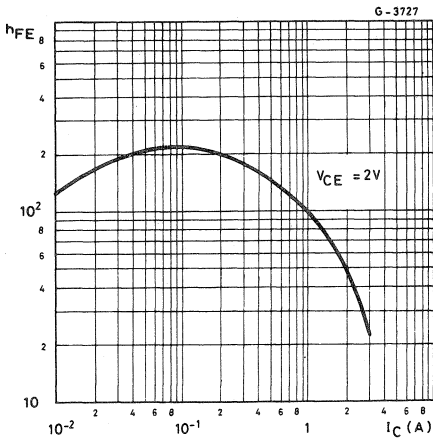


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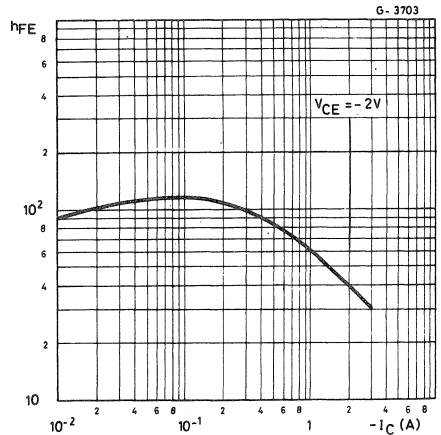
Safe operating areas



DC current gain (NPN types)



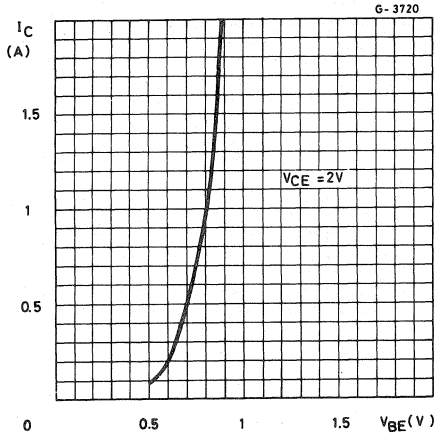
DC current gain (PNP types)



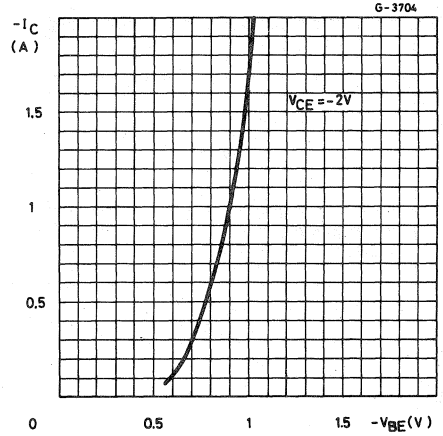


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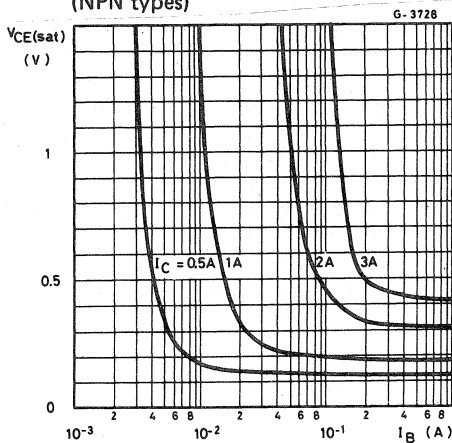
DC transconductance (NPN types)



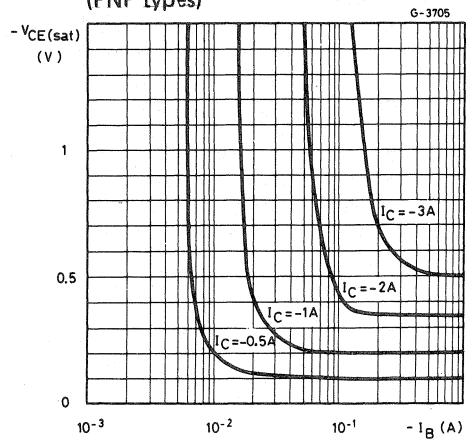
DC transconductance (PNP types)



Collector-emitter saturation voltage (NPN types)



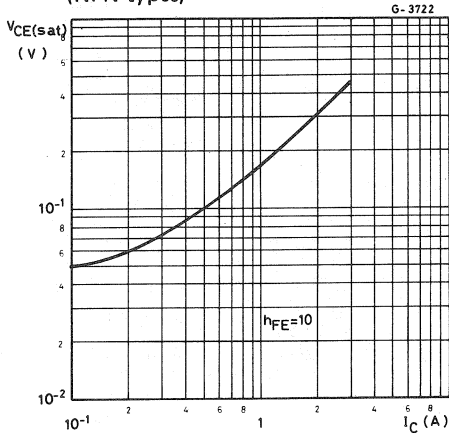
Collector-emitter saturation voltage (PNP types)



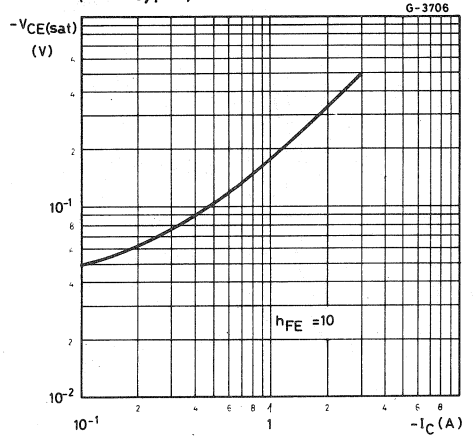


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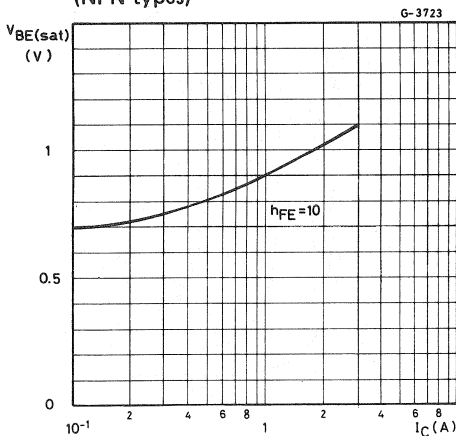
Collector-emitter saturation voltage
(NPN types)



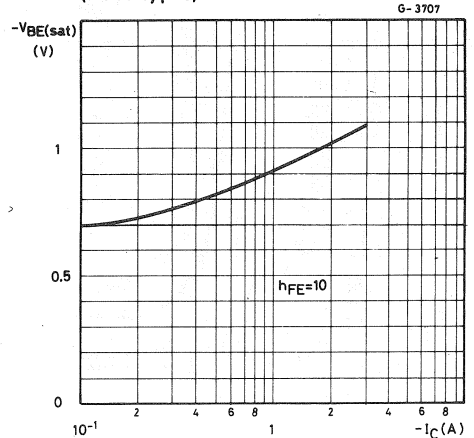
Collector-emitter saturation voltage
(PNP types)



Base-emitter saturation voltage
(NPN types)



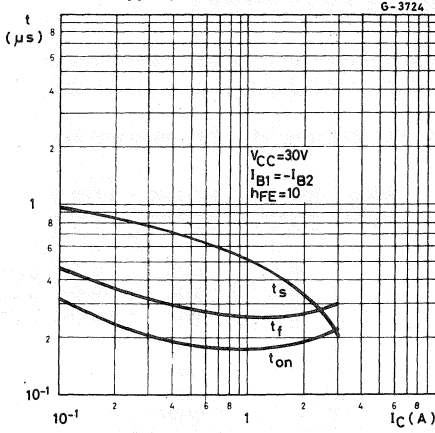
Base-emitter saturation voltage
(NPN types)



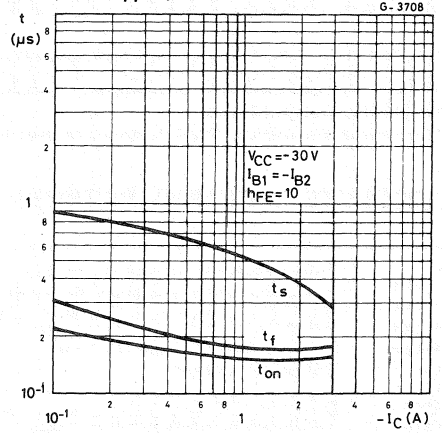


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Saturated switching characteristics
(NPN types)



Saturated switching characteristics
(NPN types)



Power derating chart

